P-Channel Enhancement Mode Power MOSFET

Description

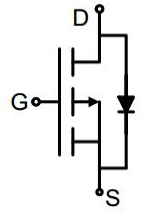
The GT100P06D5 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

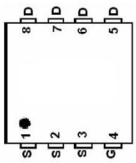
- V_{DS} -60V
- I_D (at V_{GS} = -10V) -66A
- $R_{DS(ON)}$ (at V_{GS} = -10V) < 9mΩ
- $R_{DS(ON)}$ (at V_{GS} = -4.5V) < 13mΩ
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



pin assignment



DFN5X6-8L

Ordering Information

Device	Package	Marking	Packaging
GT100P06D5	DFN5X6-8L	GT100P06	5000pcs/Reel

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-60	V
Continuous Drain Current	T_C = 25ºC	I_D	-66	A
	T_C = 100ºC		-47	
Pulsed Drain Current (note1)		I_{DM}	-264	A
Gate-Source Voltage		V_{GS}	±20	V
Power Dissipation		P_D	125	W
Single pulse avalanche energy （note2）		E_{AS}	225	mJ
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 To 175	ºC

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5	ºC/W
Maximum Junction-to-Case	R_{thJC}	1.2	ºC/W

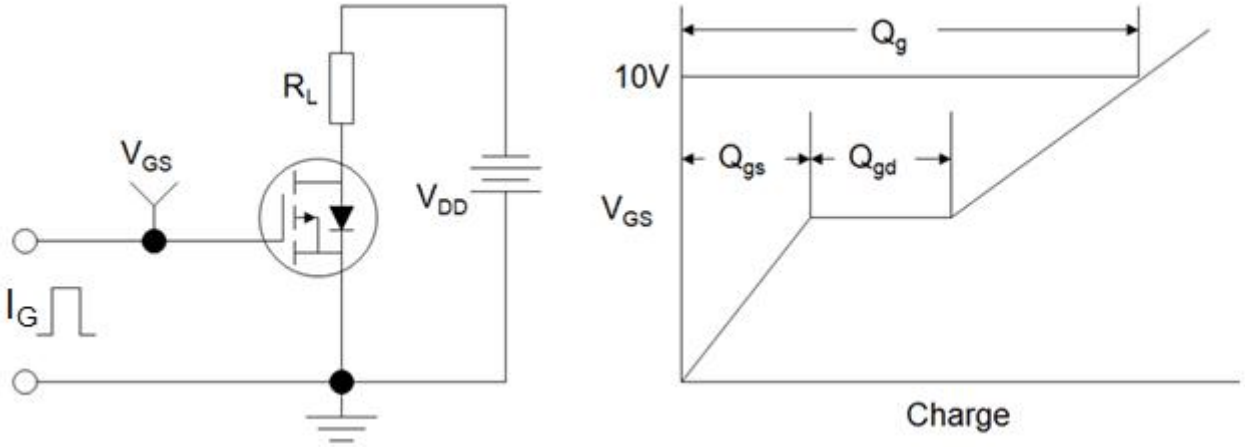
Specifications T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-60	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -60V, V_{GS} = 0V	--	--	-1	μA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1.1	-1.9	-2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = -10V, I_D = -15A	--	7.5	9	mΩ
		V_{GS} = -4.5V, I_D = -15A	--	10	13	
Forward Transconductance	g_{FS}	V_{DS} = -5V,I_D = -15A	--	29	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -30V, f = 1.0MHz	--	3700	--	pF
Output Capacitance	C_{oss}		--	645	--	
Reverse Transfer Capacitance	C_{rss}		--	32	--	
Total Gate Charge	Q_g	V_{DD} = -30V, I_D = -15A, V_{GS} = -10V	--	47	--	nC
Gate-Source Charge	Q_{gs}		--	11	--	
Gate-Drain Charge	Q_{gd}		--	9	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = -30V, I_D = -15A, R_G = 3Ω	--	4	--	ns
Turn-on Rise Time	t_r		--	2	--	
Turn-off Delay Time	$t_{d(off)}$		--	14	--	
Turn-off Fall Time	t_f		--	3	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	-66	A
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = -15A, V_{GS} = 0V	--	--	-1.2	V
Reverse Recovery Charge	Q_{rr}	I_F = -15A, V_{GS} = 0V di/dt=-100A/us	--	105	--	nC
Reverse Recovery Time	T_{rr}		--	60	--	ns

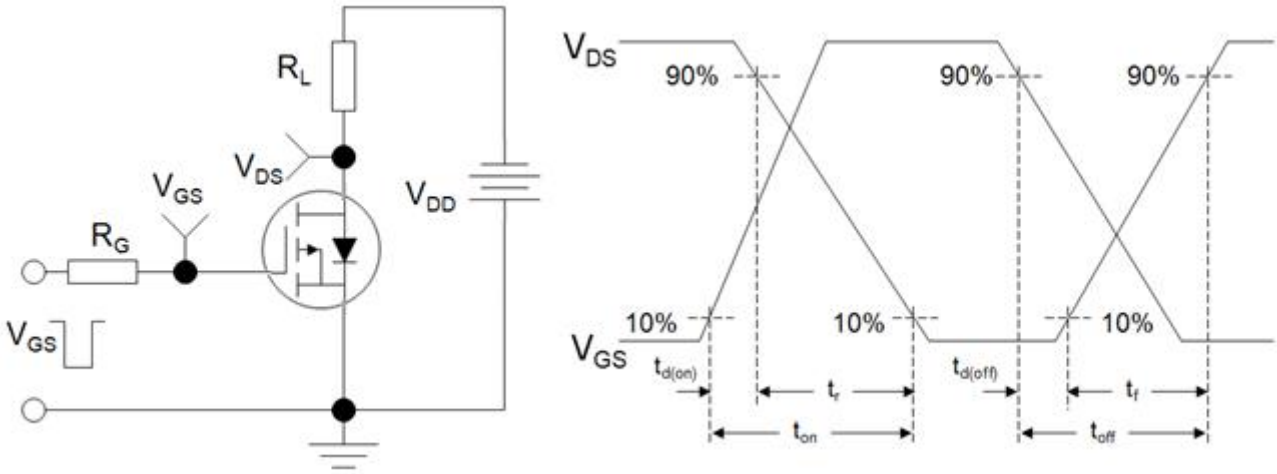
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : Tj=25℃ ,VDD=-50V,VGS=-10V,L=0.5mH,Rg=25Ω
   The table shows the minimum avalanche energy, which is 625mJ when the device is tested until failure
3. Identical low side and high side switch with identical R_G

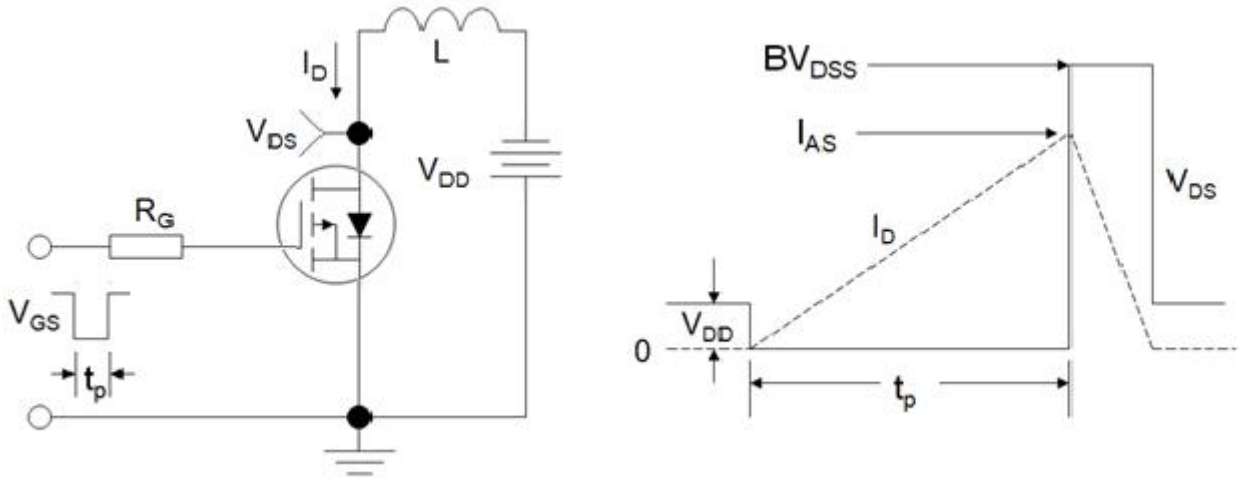
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

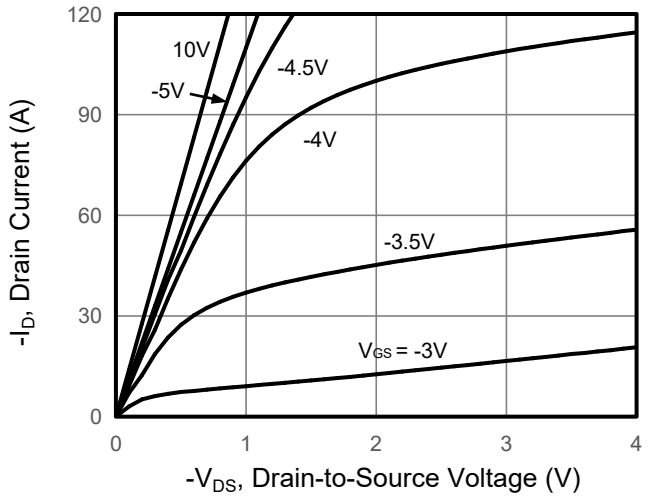


Figure 2. Transfer Characteristics

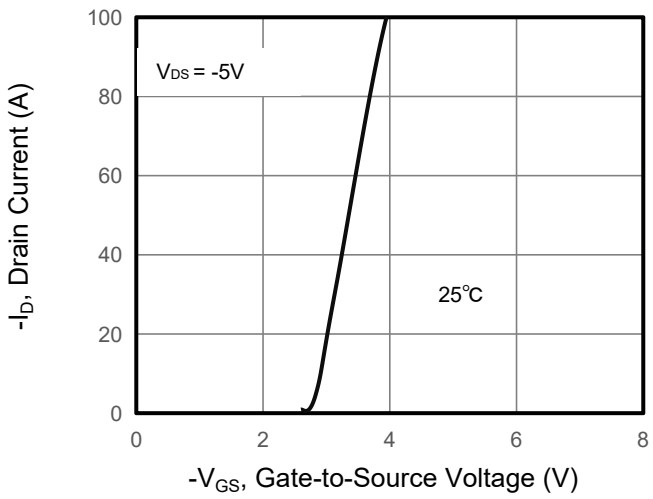


Figure 3.Drain Source On Resistance

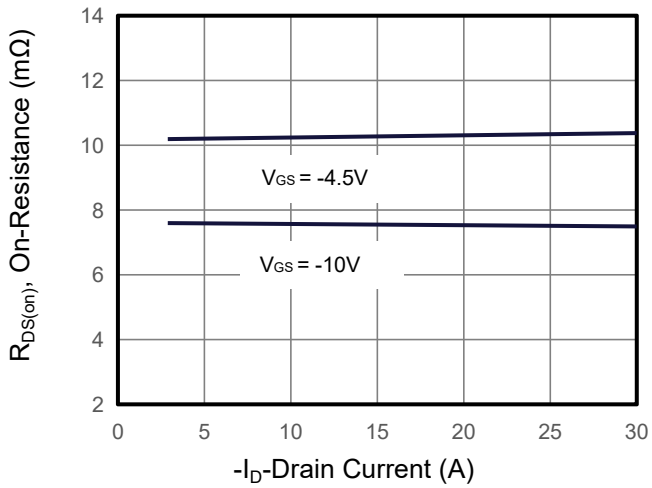


Figure 4. Gate Charge

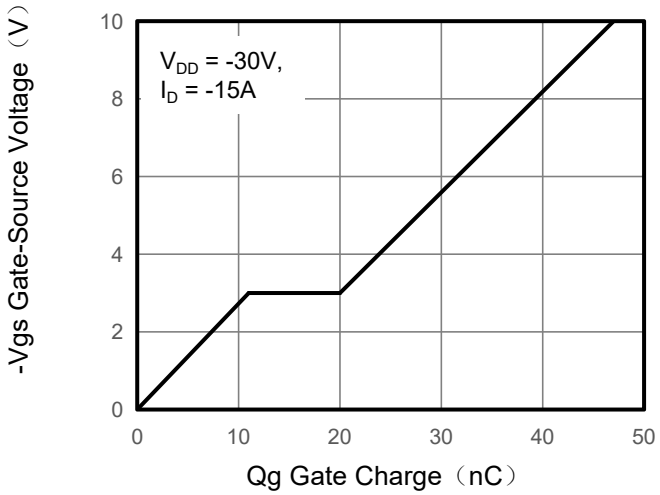


Figure 5. Capacitance

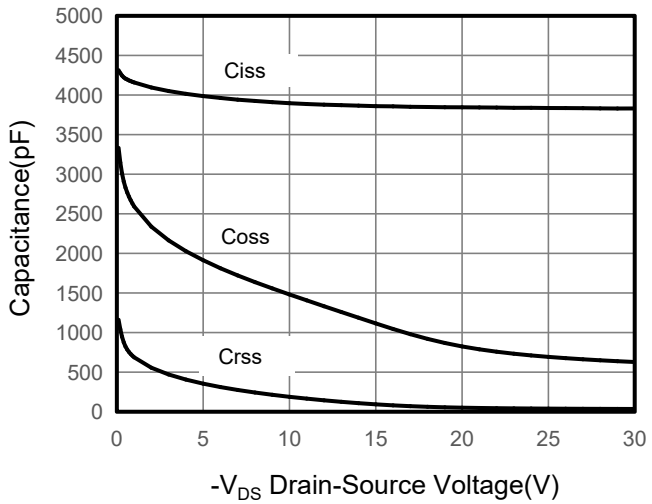
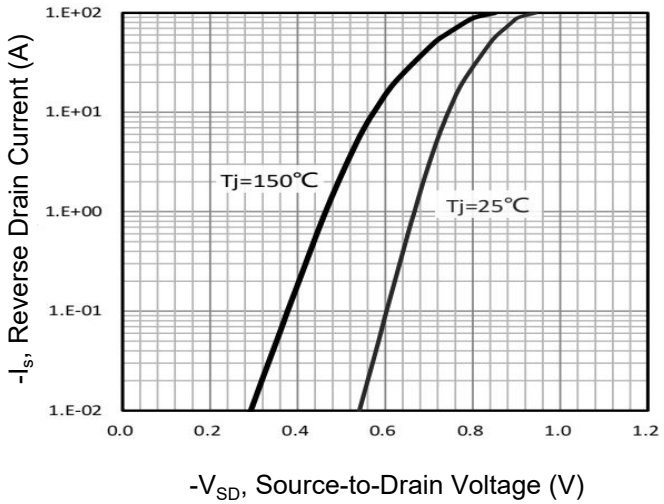


Figure 6. Source-Drain Diode Forward



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Drain-Source On-Resistance

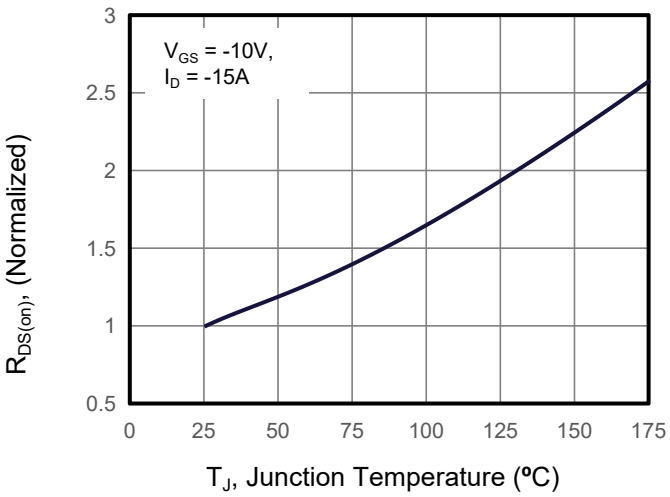


Figure 8. Safe Operation Area

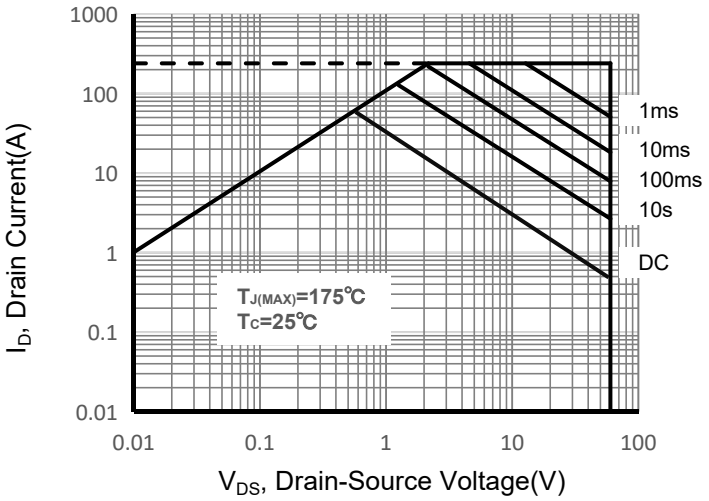


Figure 9. Maximum Continuous Drain Current vs Case Temperature

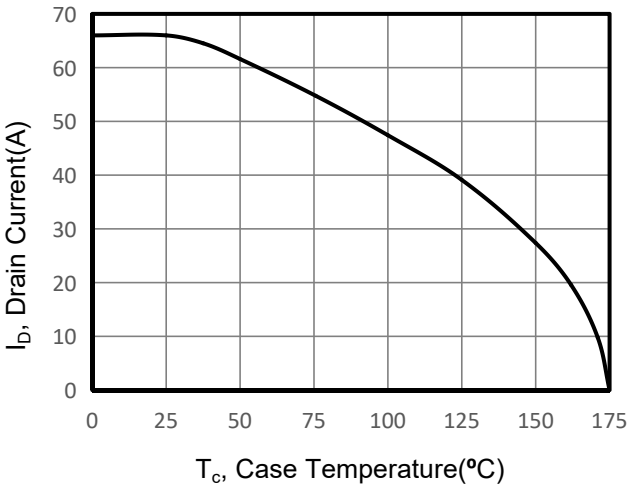
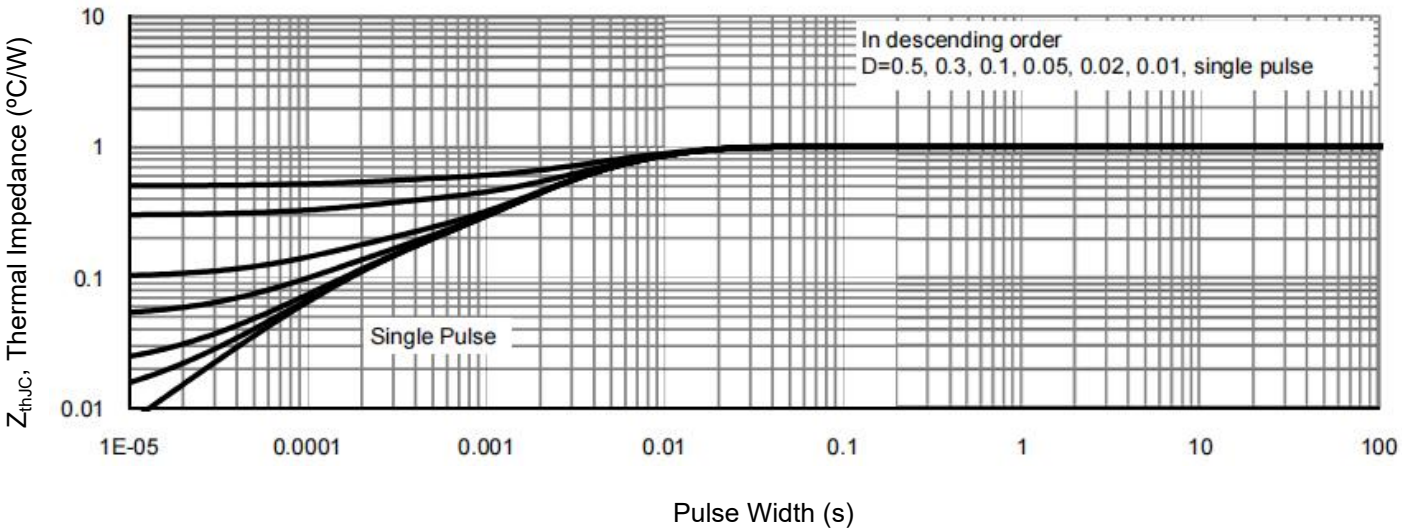
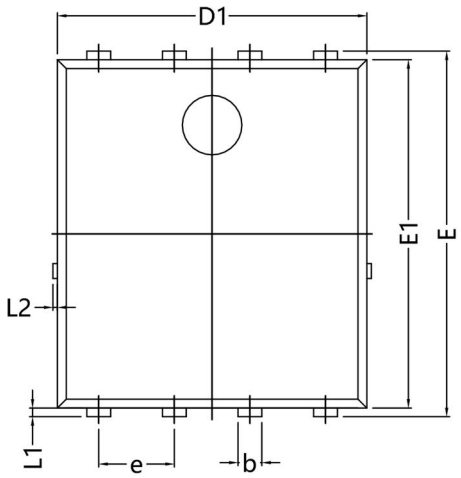


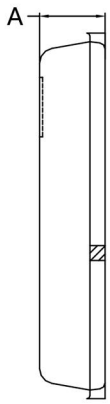
Figure 10. Normalized Maximum Transient Thermal Impedance



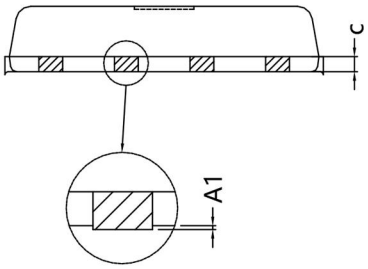
DFN5X6-8L Package Information



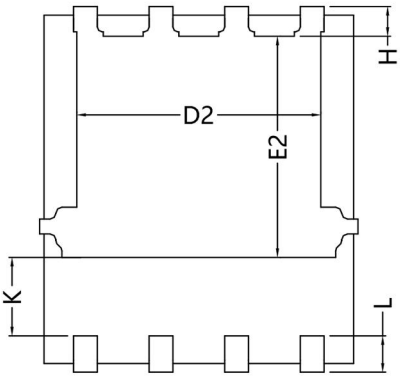
TOP VIEW



SIDE VIEW(Right)



SIDE VIEW(Front)



BOTTOM VIEW

DIM. / SYMBOL	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.00	1.10	1.20
A1	0	---	0.05
b	0.30	0.40	0.50
c	0.20	0.25	0.30
D1	5.10	5.20	5.30
D2	3.90	4.10	4.25
E	6.00	6.15	6.30
E1	5.76	5.86	5.96
E2	3.52	3.72	3.92
e	1.27 BSC		
H	0.40	0.50	0.60
L	0.50	0.61	0.71
L1	0.05	0.15	0.25
L2	0.02	0.08	0.15
K	1.10	---	---